

AMENDMENTS TO THE CLAIMS

- [1] (Original) A plasma processing apparatus, comprising:
- gas supply means for supplying a gas including a reactant gas to an interior of a chamber;
- pressure control means for controlling an internal pressure of the chamber;
- plasma generation means for generating a plasma of the gas in the interior of the chamber; and
- a susceptor, installed in a lower portion of the interior of the chamber, for supporting a substrate to be processed, and
- further comprising a wall surface protecting member, provided in the interior of the chamber, for preventing adhesion of a plasma processing-associated product onto an inner wall surface of the chamber.
- [2] (Original) The plasma processing apparatus according to claim 1, characterized in that the wall surface protecting member is an inner cylinder covering the inner wall surface of the chamber which is located above the susceptor.
- [3] (Currently amended) The plasma processing apparatus according to claim 1 ~~or 2~~, characterized in that the wall surface protecting member is supported on the chamber by point contact.
- [4] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 3~~ claim 1, characterized in that the wall surface protecting member is made of a ceramic.

[5] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 3~~ claim 1, characterized in that the wall surface protecting member is made of a metal.

[6] (Original) The plasma processing apparatus according to claim 5, characterized in that the metal is aluminum.

[7] (Currently amended) The plasma processing apparatus according to claim 5 ~~or 6~~, characterized in that the wall surface protecting member has a surface oxidized.

[8] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 7~~ claim 1, characterized in that the wall surface protecting member has a surface roughened.

[9] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 8~~ claim 1, characterized in that the gas supply means is installed while passing through a hole provided in the wall surface protecting member.

[10] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 9~~ claim 1, characterized in that a heat insulator is provided between the wall surface protecting member and the chamber.

[11] (Currently amended) The plasma processing apparatus according to ~~any one of claims 1 to 10~~ claim 1, further comprising heating means for heating a wall surface of the chamber.

[12] (Original) The plasma processing apparatus according to claim 11, characterized in that the heating means heats the wall surface of the chamber to 100°C or higher.